

Prajya

JAYPEE UNIVERSITY OF INFORMATION TECHNOLOGY, WAKNAGHAT

TEST – 1 EXAMINATION 2016

B.TECH IV SEMESTER

COURSE CODE: 10B1WEC411

COURSE NAME: Semiconductor Devices

COURSE CREDITS: 04

MAX. MARKS: 15

MAX TIME: 1HR

Roll No.....

*Note: All questions are compulsory. Carrying mobile phone during examinations will be treated as case of unfair means. Attempt questions in same order.*

- Q1. Prove that under equilibrium condition product of electron and hole concentration is equal to  $n_i^2$ . [3]
- Q2. Describe Hall Effect. How does Hall voltage help in deciding whether the semiconductor is N-type or P-type? [3]
- Q3. Define following terms: [3]
- (a). Carrier life time (b). Mean free path (c). Einstein Relationship
- Q4. In a P-type semiconductor Fermi level lies 0.4eV above the valance band edge. Determine the new position of Fermi level, if the concentration of acceptor atoms is multiplied by a factor of 0.5. Assume  $KT = 0.025\text{eV}$  [3]
- Q5. A Si bar 0.1cm long and  $100\mu\text{m}^2$  in cross sectional is doped with  $10^{17}/\text{cm}^3$  of phosphorous. Find the current at 300K with 10V applied. How long does it take an average electron to drift  $1\mu\text{m}$  in pure Si at an electric field of 100V/m? [3]